

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI FMB150** is Designed for Class C, FM Broadcast Applications up to 108 MHz.

FEATURES:

- Class C Operation
- $P_G = 9.0$ dB at 150 W/108 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CBO}	60 V
V_{CEO}	25 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	230 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.1 °C/W

PACKAGE STYLE .500 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10588

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	60			V
BV_{CER}	$I_C = 100$ mA $R_{BE} = 10 \Omega$	55			V
BV_{CEO}	$I_C = 100$ mA	25			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20		150	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			140	pF
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 150$ W $f = 108$ MHz	9.0	65		dB %